# On-Die Decoupling Model Improvements for IBIS Power Aware Models

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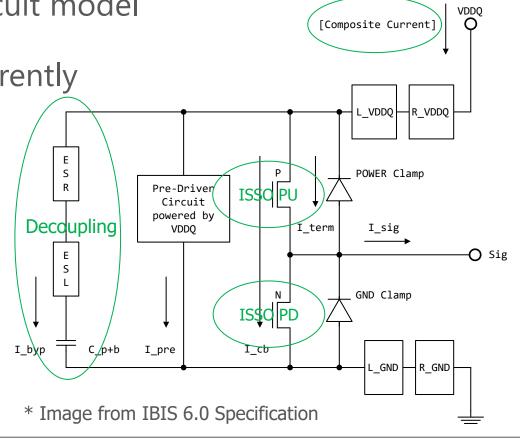
### Outline

- IBIS Power-aware modeling overview
- On-die Decoupling models
- Multi-port Decoupling models
- Example Simulations
- Conclusions



#### **IBIS Power-aware Modeling Overview**

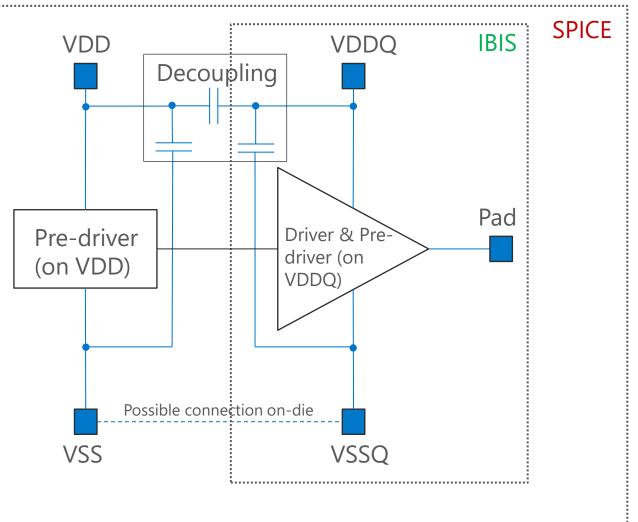
- Power Integrity modeling uses [Composite Current], [ISSO PU], [ISSO PD] and an IBIS-ISS on-die decoupling circuit model
- Decoupling model external to IBIS currently
  - I byp - Bypass current I pre - Pre-Driver current I cb - Crow-bar current I term - Termination current (optional) L VDDQ - On-die inductance of I/O Power R VDDQ - On-die resistance of I/O Power L GND - On-die inductance of Ground R GND - On-die resistance of Ground C p+b - Bypass + Parasitic Capacitance ESR - Equivalent Series Resistance for on-die Decap - Equivalent Series Inductance for on-die Decap ESL





# **On-die Decoupling Models**

- SPICE model may have pre-driver circuits on separate power supplies
- May be one common ground ondie
- Decoupling model could include VDDQ, VSSQ, VDD, VSS
- What is needed for IBIS to correlate with SPICE?



**X** 



# **Multi-port Decoupling Models**

- Decoupling circuits may contain proprietary modeling equations or process data
- A non-proprietary model can be an S-parameter or a broadband SPICE macromodel (of the S-parameter characterization)
- S-parameter port options
  - 1-port: VDDQ with VSSQ reference
  - 2-port: VDDQ, VSSQ, with 0 reference
  - 3 or [4] port: VDDQ, VSSQ, VDD, [VSS], with 0 reference



# SPICE Setup Examples for Decoupling Model Creation

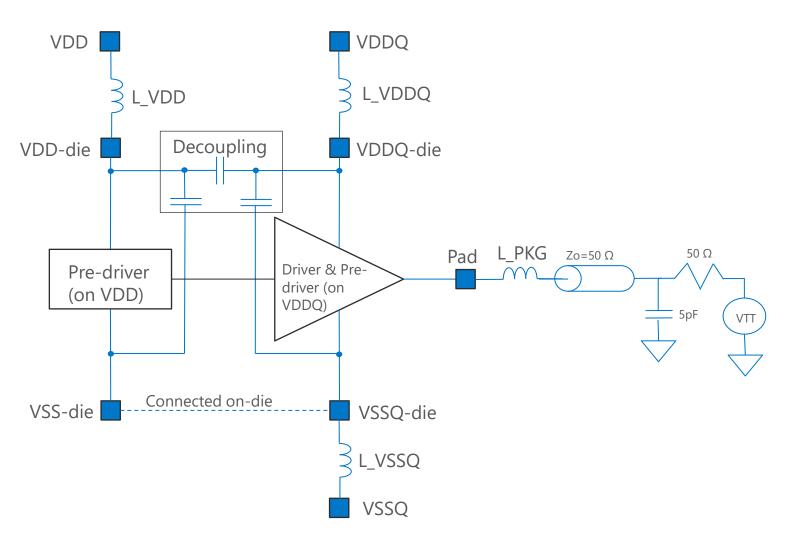
- Buffer Instance in Hi-Z state:
  - Xbuff ... VDDQ\_die VSSQ\_die ... Buffer\_name
- Port Definition:
  - Single Port
    - P1 VDDQ\_die VSSQ\_die port=1 Z0=50 DC VDDQ
  - Multi Port
    - P1 VDDQ\_die 0 port=1 Z0=50 DC VDDQ
    - P2 VSSQ\_die 0 port=2 Z0=50 DC 0
- AC Analysis

  - .ac dec 100 1 10e12



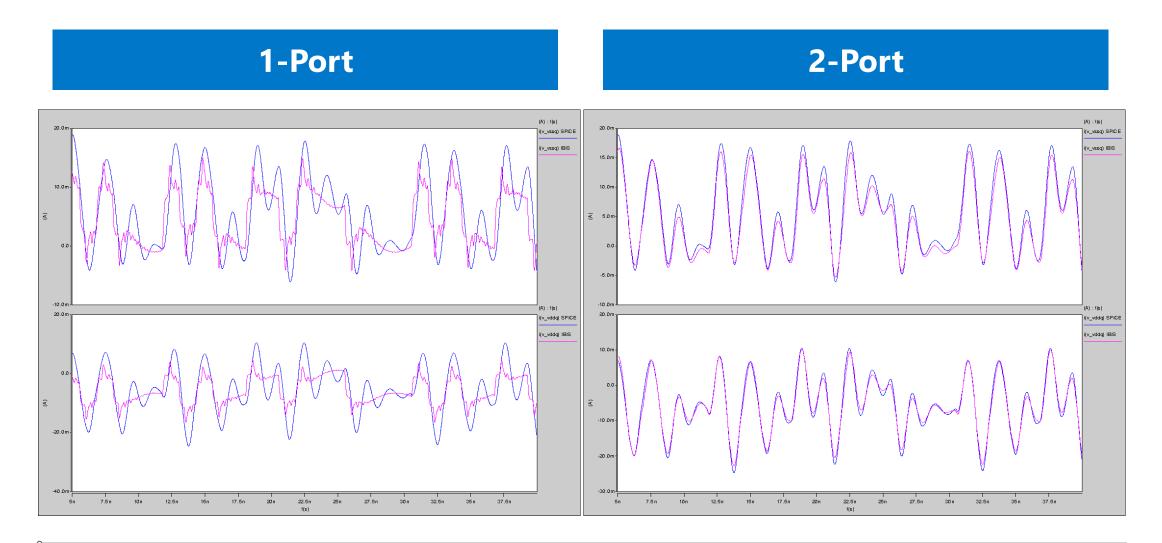
#### Example Simulation 1 – Ideal VDD Comparing Transistor-level and IBIS Model in SPICE

- L\_VDD=0 (short)
- L\_VDDQ=1.25nH
- L\_VSSQ=1.25nH
- L\_PKG=1.25nH





### 1-Port vs. 2-Port Models, I(VSSQ) and I(VDDQ)

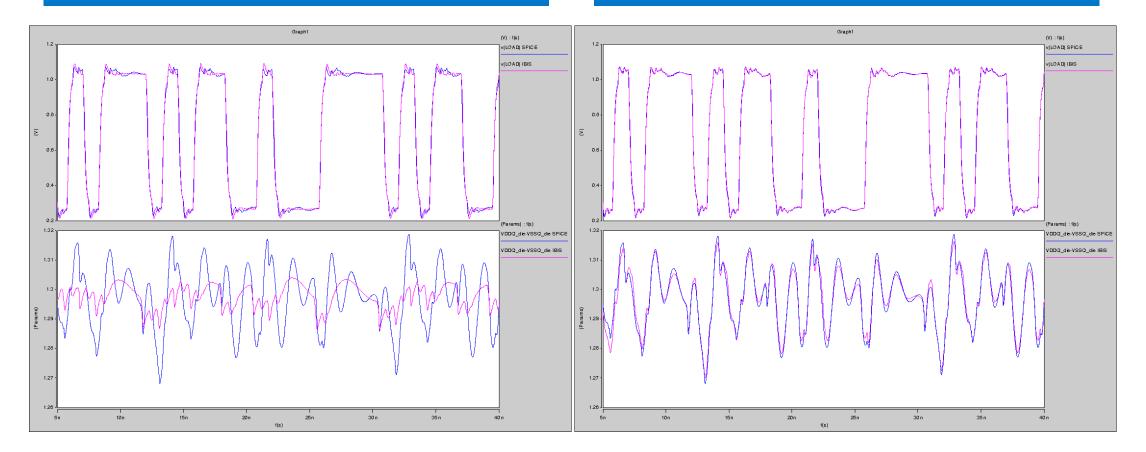




# V(LOAD) and V(VDDQ\_die)-V(VSSQ\_die)



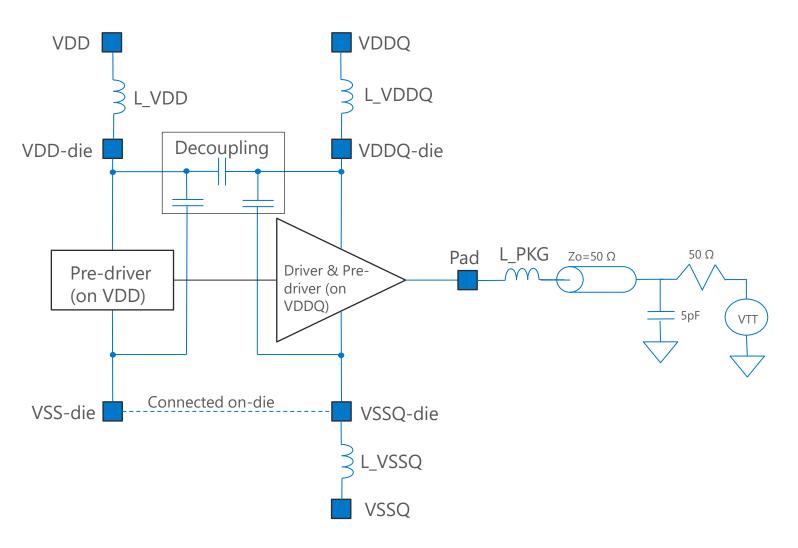
2-Port





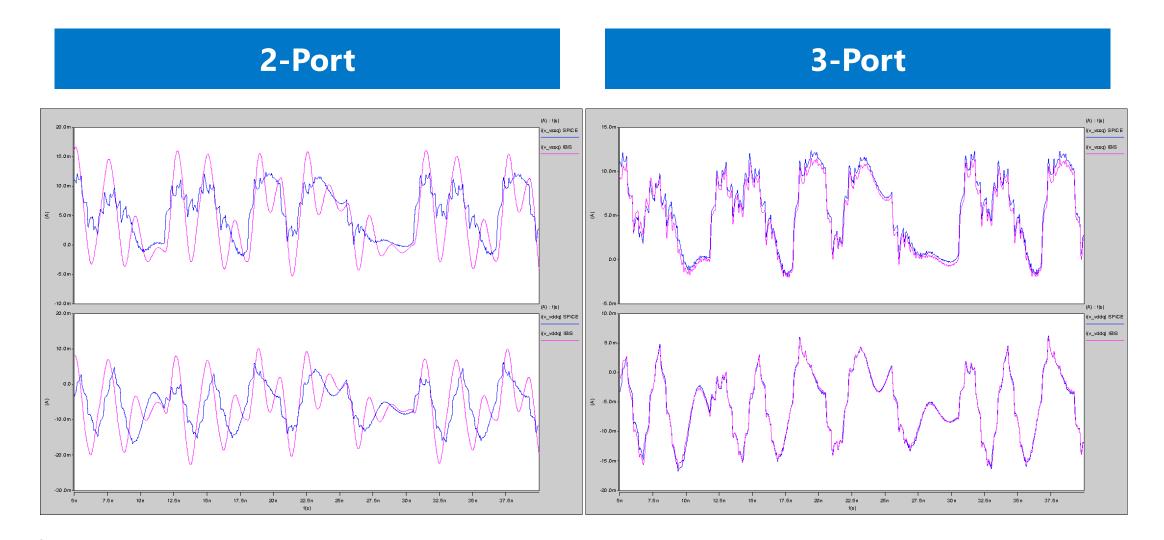
#### Example Simulation 2 – Non-ideal VDD Comparing Transistor-level and IBIS Model in SPICE

- L\_VDD=1.25nH
- L\_VDDQ=1.25nH
- L\_VSSQ=1.25nH
- L\_PKG=1.25nH





#### 2-Port vs. 3-Port Models, I(VSSQ) and I(VDDQ)

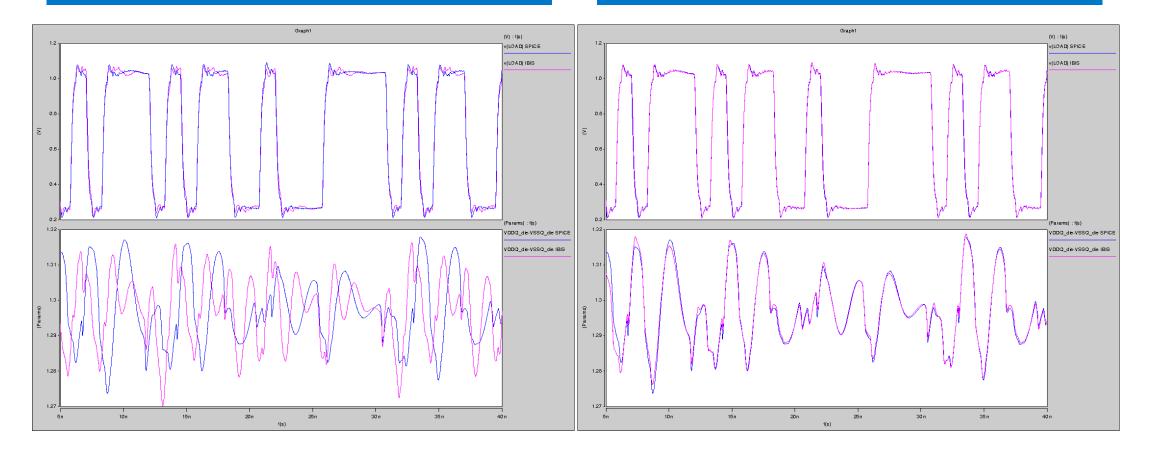




# V(LOAD) and V(VDDQ\_die)-V(VSSQ\_die)

2-Port

#### **3-Port**





### Conclusions

- A 2-port S-parameter (3-terminal macro-model) for on-die decoupling is a better model than a 1-port model for power-aware simulations.
  - This solution requires use of node 0 in the decoupling model.
- Correlating to a SPICE simulation that includes non-ideal supply connections to pre-driver circuits requires extra ports for non-ideal supplies in the decoupling model.
- A multi-port decoupling model is most versatile. Unused ports not connected to a package model should be connected to 0.
- The new IBIS Interconnect BIRD will allow the IBIS-ISS decoupling model to be connected properly to the package model.



